

BGA729N6

Broadband Low Noise Amplifier for Portable and Mobile TV Applications

Data Sheet

Revision 3.0, 2015-11-18

RF & Protection Devices

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Revision History							
Page or Item	Subjects (major changes since previous revision)						
Revision 3.0, 2	015-11-18						
9	Maximum ratings updated (Maximum value for voltage at pin AO)						
10	Input return loss updated						
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7	Marking updated						
7, 8, 10	Electrical performance updated						
11	Bill of materials updated						
12	Marking layout drawing updated						

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Broadband Low Noise Amplifier for Portable and Mobile TV Applications

BGA729N6

Features

- Insertion power gain: 16.3 dB
- Insertion Loss in bypass mode: 4.2 dB
- Low noise figure: 1.05 dB / 4.3 dB in high gain / bypass mode
- Low current consumption: 6.3 mA
- Power off function
- Operating frequency: 70 1000 MHz
- · Three-state control: OFF-, bypass- and high gain-Mode
- Supply voltage: 1.5 V to 3.3 V
- Ultra small TSNP-6-2 leadless package (footprint: 0.7 x 1.1 mm²)
- B7HF Silicon Germanium technology
- · No external matching inductor required
- RF input and output internally matched to 50 Ω
- Only 2 external SMD component necessary
- 2 kV HBM ESD protection (including Al-pin)
- Pb-free (RoHS compliant) package





Product Name	Marking	Package	
BGA729N6	M	TSNP-6-2	



Features

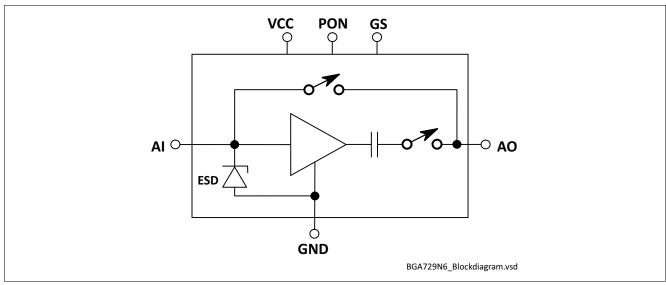


Figure 1 Block Diagram

Description

The BGA729N6 is a broadband low power low noise amplifier (LNA) MMIC for portable and mobile TV applications which covers a wide frequency range from 70 MHz to 1000 MHz. The LNA provides 16.3 dB gain and 1.05 dB noise figure at a current consumption of 6.3 mA in the application configuration described in **Chapter 3**. In bypass mode the LNA provides an insertion loss of 4.2 dB. The bypass mode with much higher linearity enables this LNA to work with much lower current consumption than commonly used TV LNAs. The BGA729N6 is based upon Infineon Technologies' B7HF Silicon Germanium technology. It operates from 1.5 V to 3.3 V supply voltage.

Pin Definition and Function

Table 1 Pin Definition and Function

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Pin No.	Function					
1	GS	High gain / bypass mode control				
2	VCC	DC supply				
3	AO	LNA output				
4	GND	Ground				
5	Al	LNA input				
6	PON	Power on / off control				

Gain Mode Selection Truth Table

Table 2 Gain Mode Selection Truth Table

Control Voltage V _{PON}	Control Voltage V _{GS}	Gain Mode	
High	Low	High Gain	
High	High	Bypass	
Low	High	Bypass	
Low	Low	OFF	



Maximum Ratings

1 Maximum Ratings

Table 3 Maximum Ratings

Parameter ¹⁾	Symbol		Value	Unit	Note /	
		Min.	Тур.	Max.		Test Condition
Voltage at pin VCC	$V_{\sf CC}$	-0.3	_	3.6	V	_
Voltage at pin Al	V_{AI}	-0.3	_	0.9	V	_
Voltage at pin AO	V_{AO}	-0.3	_	$V_{\rm CC}$ + 0.3	V	_
Voltage at pin PON	V_{PON}	-0.3	_	$V_{\rm CC}$ + 0.3	V	_
Voltage at pin GS	V_{GS}	-0.3	_	$V_{\rm CC}$ + 0.3	V	_
Voltage at GND pins	V_{GND}	-0.3	_	0.3	V	_
Current into pin VCC	I_{CC}	_	_	16	mA	_
RF input power	P_{IN}	_	_	+2	dBm	_
Total power dissipation, $T_{\rm S}$ < tbd. °C ²⁾	P_{tot}	_	_	60	mW	_
Junction temperature	T_{J}	_	_	150	°C	_
Ambient temperature range	T_{A}	-40	_	85	°C	_
Storage temperature range	T_{STG}	-65	_	150	°C	_
ESD capability all pins	$V_{\mathrm{ESD_HBM}}$	_	-	2000	V	according to JESD22A-114

¹⁾ All voltages refer to GND-Node unless otherwise noted

Attention: Stresses above the max. values listed here may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

²⁾ $T_{\rm S}$ is measured on the ground lead at the soldering point



Electrical Characteristics

2 Electrical Characteristics

Table 4 Electrical Characteristics: 1) $T_{\rm A}$ = 25 °C, $V_{\rm CC}$ = $V_{\rm PON}$ = 2.8 V, $V_{\rm GS}$ = 0 / 2.8 V, f = 70 - 1000 MHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Тур.	Max.		
Supply voltage	$V_{\sf CC}$	1.5	_	3.3	V	_
Supply current	I_{CC}	_	6.3	_	mA	High gain mode
		_	0.55	_	mA	Bypass mode
		_	0.2	5	μΑ	OFF-mode
Current into PON pin	I_{PON}	_	10	_	μΑ	High gain mode
Current into GS pin	I_{GS}	_	60	_	μΑ	Bypass mode
Insertion power gain	$ S_{21} ^2$	_	16.3	_	dB	High gain mode
f = 470 MHz		_	-4.2	_	dB	Bypass mode
Noise figure ²⁾	NF	_	1.05	_	dB	High gain mode
$Z_{\rm S}$ = 50 Ω		_	4.3	_	dB	Bypass mode
Input return loss	$RL_{\sf in}$	_	10	_	dB	High gain mode
f = 470 MHz		_	15	_	dB	Bypass mode
Output return loss	RL_{out}	_	17	_	dB	High gain mode
f = 470 MHz		_	13	_	dB	Bypass mode
Reverse isolation	$1/ S_{12} ^2$	_	28	_	dB	High gain mode
		_	4.2	_	dB	Bypass mode
Power gain settling time ³⁾	$t_{\rm S}$	_	4	_	μS	OFF- to ON-mode
Inband input 1dB-compression	IP_{1dB}	_	-15	_	dBm	High gain mode
point, f = 470 MHz		_	+6	_	dBm	Bypass mode
Inband input 3 rd -order intercept	IIP_3	_	-6	_	dBm	High gain mode
point ⁴⁾ $f_1 = 470 \text{ MHz}, f_2 = f_1 + 1 \text{ MHz}$		-	+20	_	dBm	Bypass mode
Stability	k	_	> 1	_		f = 20 MHz 10 GHz

¹⁾ Based on the application described in chapter 3

²⁾ PCB losses are subtracted

³⁾ To be within 1 dB of the final gain

⁴⁾ High gain mode: Input power = -30 dBm for each tone / Bypass mode: Input power = -10 dBm for each tone



Application Information

3 Application Information

Application Board Configuration

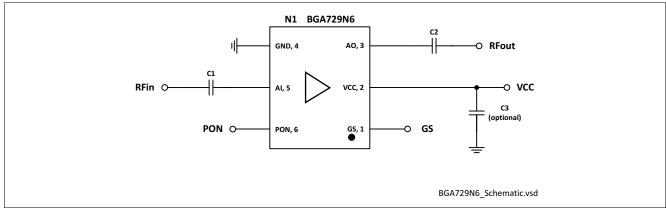


Figure 2 Application Schematic BGA729N6

Table 5 Bill of Materials

Name	Value	Package	Manufacturer	Function
C1	1 nF	0402	Various	DC block 1)
C2	1 nF	0402	Various	DC block 1)
C3 (optional)	≥ 1 nF	0402	Various	RF bypass ²⁾
N1	BGA729N6	TSNP-6-2	Infineon	SiGe LNA

¹⁾ DC block might be necessary due to internal LNA bias voltage @ AI (LNA Analog Input pin). The DC block can be realized with pre-filter (e.g. SAW)

Note: No external DC blocking capacitor at RFout is required in typical applications as long as no DC is applied.

A list of all application notes is available at http://www.infineon.com/Itelna

²⁾ RF bypass recommended to mitigate power supply noise



Package Information

4 Package Information

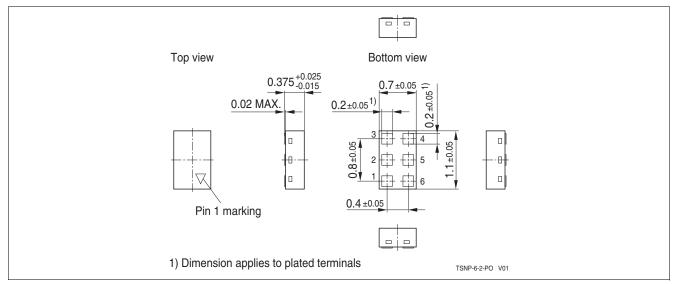


Figure 3 TSNP-6-2 Package Outline (top, side and bottom views)

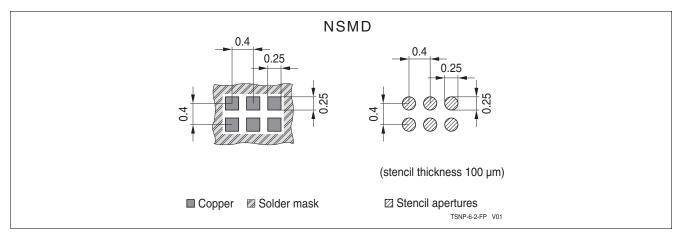


Figure 4 Footprint Recommendation TSNP-6-2

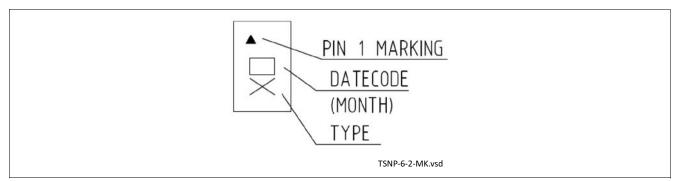


Figure 5 Marking Layout (top view)



Package Information

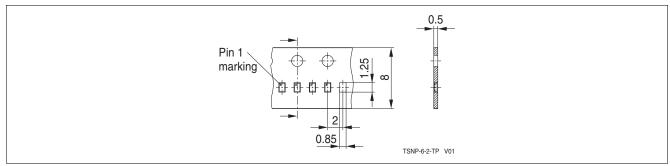


Figure 6 Tape & Reel Dimensions (reel diameter 180 mm, pieces/reel 15000)

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